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(54) **Title**: NON-PLANAR TRANSISTORS AND METHODS OF FABRICATION THEREOF

(57) **Abstract**: The present description relates to the formation source/drain structures within non-planar transistors, wherein fin spacers are removed from the non-planar transistors in order to form the source/drain structures from the non-planar transistor fins or to replace the non-planar transistor fins with appropriate materials to form the source/drain structures.

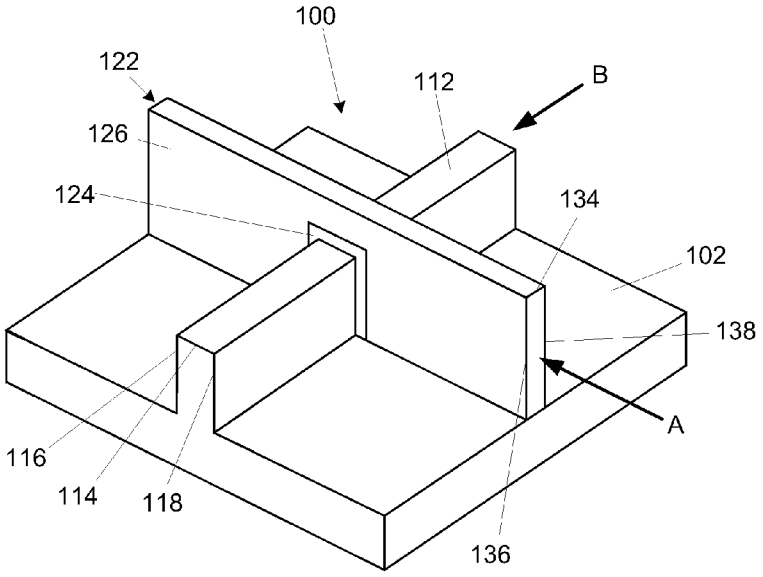


FIG. 1

WO 2013/048455 A1